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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 3 of 7

Complete if Known	
Application Number	Not yet assigned 10691026
Filing Date	March 9, 2006
First Named Inventor	Jonathan J. Wierer Jr.
Art Unit	Not yet assigned
Examiner Name	Not yet assigned
Attorney Docket Number	LUM-03-03-02-1C

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
SC		J.J. WIERER et al., "InGaN/GaN quantum-well heterostructure light-emitting diodes employing photonic crystal structures," Applied Physics Letters, Vol. 84, No. 19, May 10, 2004, pp. 3885-3887.	
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↓		Vuckovic et al., "Surface Plasmon Enhanced Light Emitting Diode," Journal of Quantum Electronics, Vol. 36, 2000, pp. 1-13.	
SC		Tredicucci et al., "Single-mode surface-plasmon laser," Applied Physics Letters, Vol. 76, No. 16, April 17, 2000, pp. 2164-2166.	

Examiner Signature	/Sara Crane/	Date Considered	06/25/2006

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Sheet 4 of 7

Complete if Known	
Application Number	Not yet assigned 10691026
Filing Date	March 9, 2006
First Named Inventor	Jonathan J. Wierer Jr.
Art Unit	Not yet assigned
Examiner Name	Not yet assigned
Attorney Docket Number	LUM-03-03-02-1C

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SC		Imada et al., "Coherent two-dimensional lasing action in surface-emitting laser with triangular-lattice photonic cyrstal structure," Applied Physics Letters, Vol. 75, No. 3, July 19, 1999, pp. 316-318.	
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		T. FUJII et al., "Increase in the extraction efficiency of GaN-based light-emitting diodes via surface roughening", Applied Physics Letters, Vol. 84, No. 6, 9 February 2004, pp. 855-857.	
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Sheet 5 of 7

Complete if Known	
Application Number	10/691,026
Filing Date	October 21, 2003
First Named Inventor	Jonathan J. Wierer Jr.
Art Unit	2811
Examiner Name	Sara W. Crane
Attorney Docket Number	LUM-03-03-02

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SC		J. RISTIC et al., "Characterization of GaN quantum discs embedded in AlxGa1-xN nanocolumns grown by molecular beam epitaxy," Physical Review B68, (2003), The American Physical Society, pp. 125305-1 to 125305-5.	
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Examiner Signature	/Sara Crane/	Date Considered	06/25/2006

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Sheet 6 of 7

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Application Number	Not yet assigned 10691026
Filing Date	March 9, 2006
First Named Inventor	Jonathan J. Wierer Jr.
Art Unit	Not yet assigned
Examiner Name	Not yet assigned
Attorney Docket Number	LUM-03-03-02-1C

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SC		V.V. MAMUTIN, et al., "Growth of Self-Organized GaN Nanostructures on Al2O3 (0001) by RF MBE," Proc. Int. Workshop on Nitride Semiconductors, IPAP Conf. Series 1, pp. 413 to 416.		considered, but no date provided
		J. SU et al., "Catalytic growth of group III-nitride nanowires and nanostructures by metalorganic chemical vapor deposition," Applied Physics Letters 86, (2005), American Institute of Physics, pp. 013105-1 to 013105-3.		
		W. D. ZHOU et al, "Electrically injected single-defect photonic bandgap surface-emitting laser at room temperature," Electronic Letters, 31st August 2000, Vol. 36, No. 18, pp. 1541 to 1542.		
		P. BHATTACHARYA et al., "Electrically Injected Photonic Bandgap Microcavity Light Sources," LEOS 2001 14th. Annual Meeting of the IEEE Lasers & Electro-Optics Society, San Diego, Ca, Nov. 11-15, Vol 1 of 2, pp. 76 to 77.		
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Sheet 7 of 7

Complete if Known	
Application Number	Not yet assigned 10691026
Filing Date	March 9, 2006
First Named Inventor	Jonathan J. Wierer J
Art Unit	Not yet assigned
Examiner Name	Not yet assigned
Attorney Docket Number	LUM-03-03-02-1C

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SC		HIROYUKI ICHIKAWA et al., "Efficiency enhancement in a light-emitting diode with a two-dimensional surface grating photonic cyrstal," Applied Physics Letters, Vol. 84, No. 4, 26 January 2004, pp. 457-459.	
SC		~~European Search Report, 4 pages.~~ considered, but no date provided	

Examiner Signature	/Sara Crane/	Date Considered	06/25/2006

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